

Amendments to the Claims:

Please cancel claims 2, 3, 9, 10, 14 and 18, which stand withdrawn from consideration without prejudice or disclaimer of the subject matter thereof and without prejudice to the right to file a divisional application thereon.

Please claim 19 without prejudice or disclaimer of the subject matter thereof, amend claim 1 and add the following new claims.

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A liquid crystal display device including thin film transistors and pixel electrodes formed on a substrate being characterized in that each thin film transistor includes a silicon film, a gate electrode, and a source electrode which is electrically connected to the pixel electrode, between the silicon film and the substrate and between the pixel electrode and the substrate, a silicon oxide film and a silicon nitride film ~~which is~~ are formed, the silicon nitride film being formed between the silicon oxide film and the substrate ~~are interposed~~, and a film thickness of the silicon nitride film is larger than a film thickness of the silicon oxide film.

Claim 2 (canceled)

Claim 3 (canceled)

4. (original) A liquid crystal display device according to claim 1, wherein the film thickness of the silicon nitride film falls within a range of 130nm to 160nm.

5. (original) A liquid crystal display device according to claim 1, wherein the film thickness of the silicon nitride film falls within a range of 126nm to 165nm.

6. (original) A liquid crystal display device according to claim 1, wherein a gate insulation film is formed between the silicon layer and the gate electrode, and an interlayer film arranged close to the gate insulation film is interposed between the gate insulation film and the pixel electrode.

7. (original) A liquid crystal display device according to claim 6, wherein the interlayer film includes a first interlayer insulation film and a second interlayer insulation film which is formed between the first interlayer insulation film and the pixel electrode.

8. (original) A liquid crystal display device according to claim 7, wherein the gate insulation film and the first interlayer insulation film are made of a same material.

Claim 9 (canceled)

Claim 10 (canceled)

11. (original) A liquid crystal display device according to claim 1, wherein the pixel electrode includes a reflective electrode and a light-transmissive electrode, and a distance from the substrate to the reflective electrode and a distance from the substrate to the light-transmissive electrode differ from each other.

12. (original) A liquid crystal display device according to claim 11, wherein an organic film is formed between the reflective electrode and the substrate.

13. (original) A liquid crystal display device according to claim 1, wherein the pixel electrode is a light transmissive electrode and an organic film is formed between the light transmissive electrode and the substrate.

Claim 14 (canceled)

15. (original) A liquid crystal display device according to claim 1, wherein light transmissive counter electrodes are formed on a substrate which faces the substrate in an opposed manner.

16. (original) A liquid crystal display device according to claim 13, wherein a backlight is formed outside the substrate and a reflector is formed on the backlight.

17. (original) A liquid crystal display device according to claim 1, wherein the pixel electrode is formed on an organic film formed on the substrate and a common electrode is also formed on the organic film.

Claim 18 (canceled)

Claim 19 (canceled)

20. (new) A liquid crystal display device according to claim 1, wherein the silicon nitride film and the silicon oxide film are configured so as to reduce reflection light from a transmissive region of the liquid crystal display device.

21. (new) A liquid crystal display device comprising:

a first glass substrate;

a second glass substrate;

a first silicon nitride film formed on the first glass substrate;
a first silicon oxide film formed on the first silicon nitride film;
a gate insulating film formed over the first silicon oxide film;
a polysilicon film formed between the first silicon oxide film and the gate insulating film;
a gate electrode formed over the gate insulating film;
an interlayer insulating film formed over the gate electrode and the gate insulating film;
a transmissive region comprising a transparent pixel electrode formed over the interlayer insulating film, and electrically connected to the polysilicon film; and
a backlight and a reflector formed outside the first glass substrate;
wherein the first silicon nitride film and the first silicon oxide film are formed between the transparent pixel electrode and the first glass substrate; and
wherein a film thickness of the first silicon nitride film is larger than a film thickness of the first silicon oxide film, and the film thickness of the first silicon nitride film falls within a range of 118nm and 169nm.

22. (new) A liquid crystal display device according to claim 21, wherein the film thickness of the first silicon nitride film falls within a range of 130nm to 160nm.

23. (new) A liquid crystal display device according to claim 21, further comprises a reflective layer formed over the interlayer insulating film, wherein a distance from the first substrate to a region of a part of the transparent pixel electrode and a distance from the first substrate to a region of the reflective layer differ from each other.

24. (new) A liquid crystal display device according to claim 21, wherein a light from outside of the second glass substrate is reflected by the reflector formed outside the first glass substrate.

25. (new) A liquid crystal display device according to claim 21,
wherein the interlayer insulating film includes a first interlayer insulating film and a second interlayer insulating film which is formed between the first interlayer insulating film and the transparent pixel electrode, and
wherein the second interlayer insulating film are made of silicon nitride, and a thickness of the second interlayer insulating film falls within a range of 118nm to 169nm or 268nm to 319nm.

26. (new) A liquid crystal display device according to claim 21, wherein the first silicon nitride film and the first silicon oxide film are configured so as to reduce reflection light from the transmissive region of the liquid crystal display device.